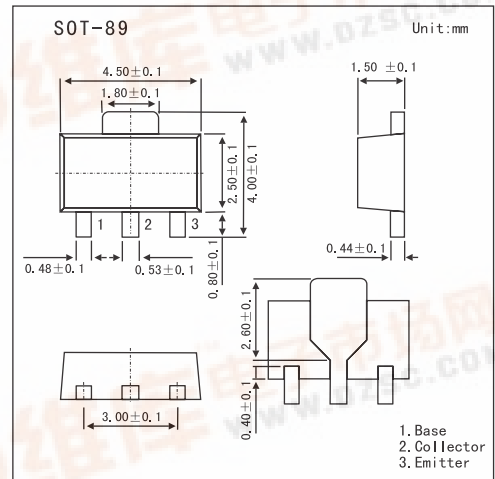


SMD Type Transistors

Silicon PNP Epitaxial Planar Type
2SB1539

■ Features

- Low collector to emitter saturation voltage $V_{CE(sat)}$.
- Large collector power dissipation P_C .
- Mini Power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-20	V
Collector-emitter voltage	V_{CEO}	-20	V
Emitter-base voltage	V_{EBO}	-5	V
Peak collector current	I_{CP}	-1.2	A
Collector current	I_C	-1	A
Collector power dissipation	P_C	1	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = -7\text{ V}, I_E = 0$			-1	μA
Collector-base voltage	V_{CBO}	$I_C = -10\ \mu\text{A}, I_E = 0$	-20			V
Collector-emitter voltage	V_{CEO}	$I_C = -1\ \text{mA}, I_B = 0$	-20			V
Emitter-base voltage	V_{EBO}	$I_E = -10\ \mu\text{A}, I_C = 0$	-5			V
Forward current transfer ratio	h_{FE}	$V_{CE} = -2\ \text{V}, I_C = -100\ \text{mA}$	200		800	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500\ \text{mA}, I_B = -10\ \text{mA}$			-0.2	V
Transition frequency	f_T	$V_{CB} = -10\ \text{V}, I_E = 50\ \text{mA}, f = 200\ \text{MHz}$		120		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10\ \text{V}, I_E = 0, f = 1\ \text{MHz}$		30		pF

■ Marking

Marking	1N
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